STC04IE170HV

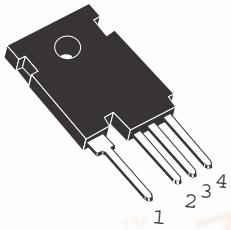
Emitter switched bipolar transistor
ESBT® 1700V - 4A - 0.17 Ω

General features

Table 1. General features

$V_{CS(ON)}$	I_C	$R_{CS(ON)}$
0.7V	4A	0.17Ω

- High voltage / high current cascode configuration
- Low equivalent on resistance
- Very fast-switch, up to 150 kHz
- Squared RBSOA, up to 1700 V
- Very low C_{ISS} driven by R_G = 47 Ω
- Very low turn-off cross over time
- In compliance with the 2002/93/EC European Directive

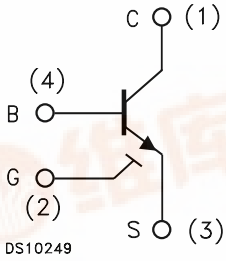


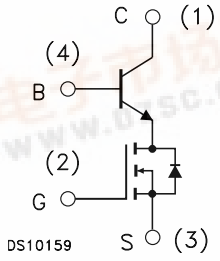
TO247-4L HV

Description

The STC04IE170HV is manufactured in Monolithic ESBT technology, aimed to provide the best performance in High Frequency / High voltage applications. It is designed for use in Gate Driven based topologies.

Internal schematic diagrams





Applications

- Aux SMPS for three phase mains

Order codes

Part Number	Marking	Package	Packing
STC04IE170HV	C04IE170HV	TO247-4L HV	Tube

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
$V_{CS(SS)}$	Collector-source voltage (V_{BS} =V_{GS} =0V)	1700	V
$V_{BS(OS)}$	Base-source voltage (I_C =0, V_{GS} =0V)	30	V
$V_{SB(OS)}$	Source-base voltage (I_C =0, V_{GS} =0V)	17	V
V_{GS}	Gate-source voltage	± 17	V
I_C	Collector current	4	A
I_{CM}	Collector peak current (t_P < 5ms)	15	A
I_B	Base current	2	A
I_{BM}	Base peak current (t_P < 1ms)	4	A
P_{tot}	Total dissipation at $T_c \leq 25°C$	178	W
T_{stg}	Storage temperature	-40 to 150	°C
T_J	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter		Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	max	0.7	°C/W

2 Electrical characteristics

(T_{case} = 25°C unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CS(SS)}$	Collector-source current (V_{BS} =V_{GS} =0V)	$V_{CS(SS)}$ =1700V			100	µA
$I_{BS(OS)}$	Base-source current (I_C =0, V_{GS} =0V)	$V_{BS(OS)}$ =30V			10	µA
$I_{SB(OS)}$	Source-base current (I_C =0, V_{GS} =0V)	$V_{SB(OS)}$ =17V			100	µA
$I_{GS(OS)}$	Gate-source leakage (V_{BS} =0V)	V_{GS} = ± 17V			100	nA
$V_{CS(ON)}$	Collector-source ON voltage	V_{GS} =10V I_C =4A I_B =0.8A V_{GS} =10V I_C =1.5A I_B =0.15A		0.7 0.6	1.5 1.4	V V
h_{FE}	DC current gain	V_{CS} =1V V_{GS} =10V I_C =4A V_{CS} =1V V_{GS} =10V I_C =1.5A	4 7	5.5 11		
$V_{BS(ON)}$	Base-source ON voltage	V_{GS} =10V I_C =4A I_B =0.8A V_{GS} =10V I_C =1.5A I_B =0.15A		1.3 0.9	1.5 1.1	V V
$V_{GS(th)}$	Gate threshold voltage	V_{BS} =V_{GS} I_B =250µA	2	3	4	V
C_{iss}	Input capacitance	V_{CS} =25V f =1MHz V_{GS}=0V		510		pF
$Q_{GS(tot)}$	Gate-source Charge	V_{GS}=10V		3.9		nC
t_s t_f	INDUCTIVE LOAD Storage time Fall time	V_{GS} =10V R_G =47Ω V_{Clamp} =1360V t_p =4µs I_C =2A I_B =0.4A		770 10		ns ns
t_s t_f	INDUCTIVE LOAD Storage time Fall time	V_{GS} =10V R_G =47Ω V_{Clamp} =1360V t_p =4µs I_C =2A I_B =0.2A		410 10		ns ns
$V_{CS(dyn)}$	Collector-source dynamic voltage (500ns)	V_{CC} =V_{Clamp} =400V V_{GS} =10V I_C =1.5A I_B = 0.3A t_{peak} =500ns R_G =47Ω I_{Bpeak} =3A (2I_C)		5.36		V

Table 4. Electrical characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CS(dyn)}$	Collector-source dynamic voltage (1µs)	V_{CC} =V_{Clamp} =400V V_{GS} =10V I_C = 1.5A I_B = 0.3A t_{peak} =500ns R_G =47Ω I_{Bpeak} = 3A (2I_C)		4.32		V
V_{CSW}	Maximum collector-source voltage switched without snubber	R_G =47Ω h_{FE} =5 I_C = 4A	1700			V

Note (1) Pulsed duration = 300 µs, duty cycle ≤1.5%

2.1 Electrical characteristics (curves)

Figure 1. Output characteristics

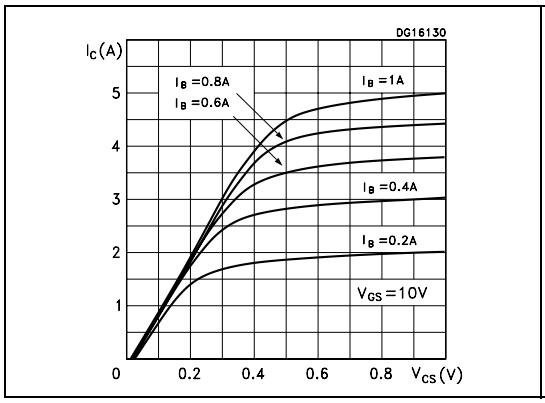


Figure 2. Dynamic collector-source saturation voltage

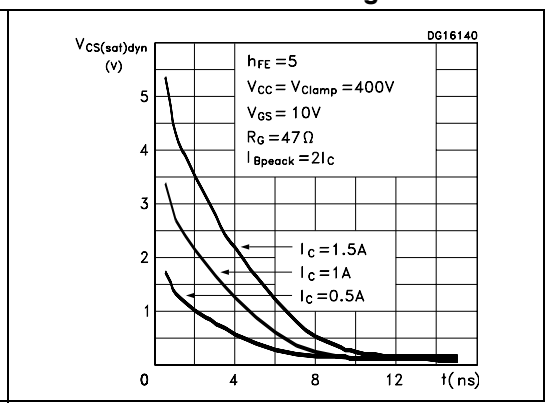


Figure 3. DC current gain

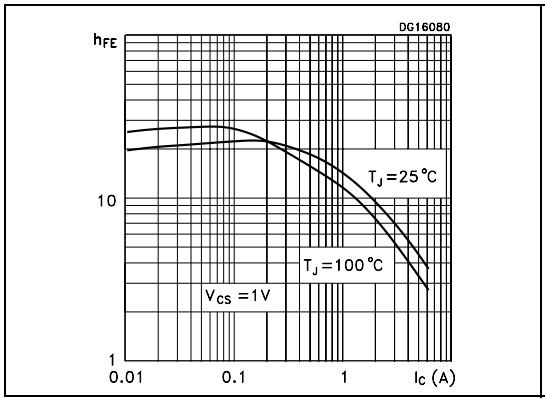


Figure 4. Gate threshold voltage vs temperature

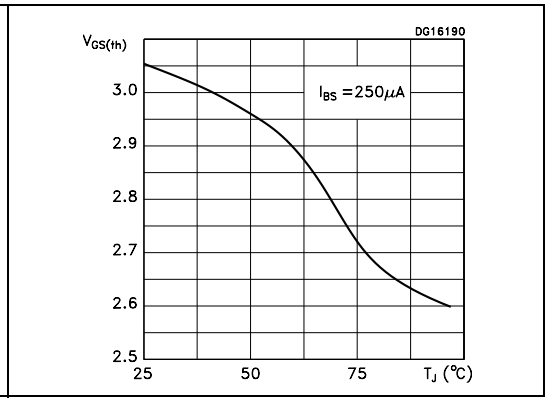


Figure 5. Collector-source On voltage

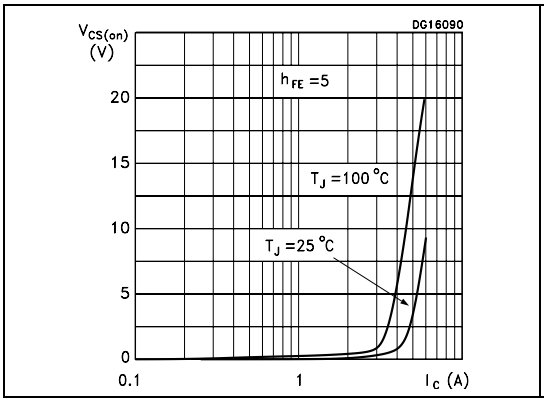


Figure 6. Collector-source On voltage

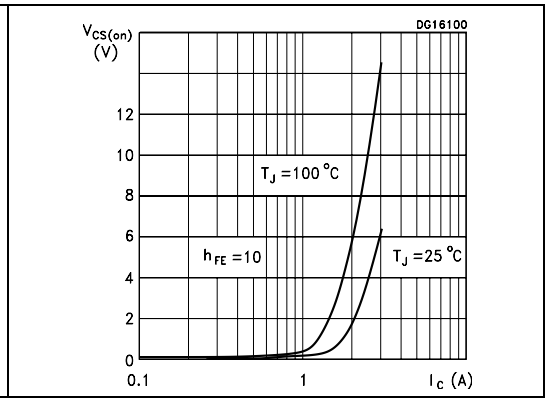


Figure 7. Base-source On voltage

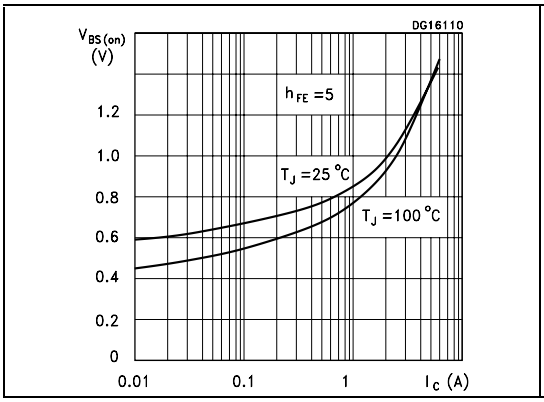


Figure 8. Base-source On voltage

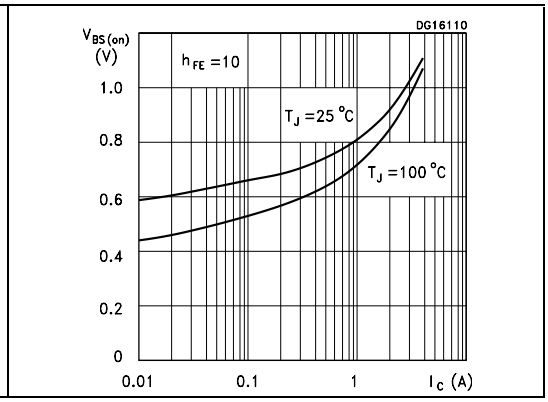


Figure 9. Inductive load switching time

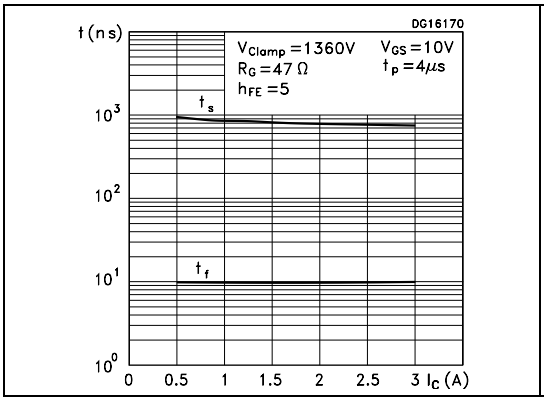


Figure 10. Inductive load switching time

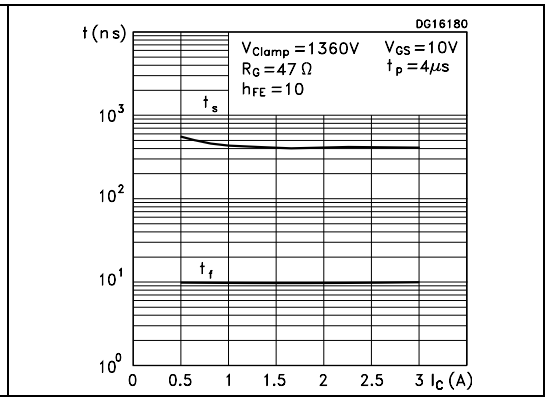
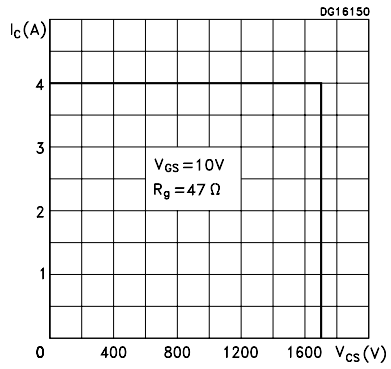


Figure 11. Reverse biased safe operating area

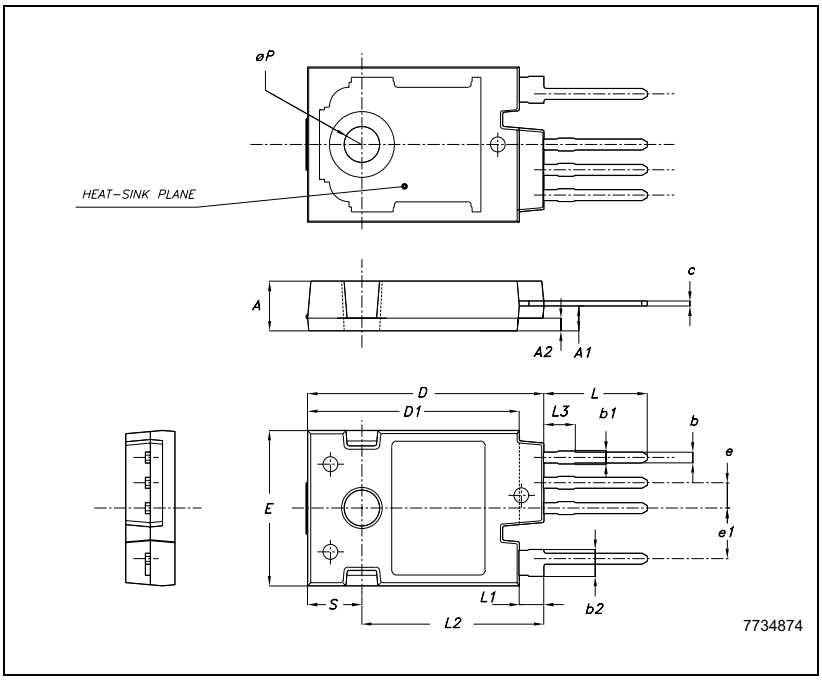


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO247-4L HV MECHANICAL DATA

DIM.	mm.		
	MIN.	TYP	MAX.
A	4.85		5.15
A1	2.20	2.50	2.60
A2		1.27	
b	0.95	1.10	1.30
b2	2.50		2.90
c	0.40		0.80
D	23.85	24	24.15
D1		21.50	
E	15.45	15.60	15.75
e	2.54		
e1	5.08		
L	10.20		10.80
L1	2.20	2.50	2.80
L2		18.50	
L3		3	
øP	3.55		3.65
S		5.50	



4 Revision history

Table 5. Revision history

Date	Revision	Changes
11-Sep-2006	1	First release.
21-Nov-2006	2	Improved application target.

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